

IN THE SPECIFICATION

Please replace the title of this application with the following title:

--MANUFACTURING METHOD OF SEMICONDUCTOR MODULE--

On Page 29, replace the second full paragraph with the following:

--In this manner, according to the present invention, it is sufficient to supply a small quantity of the low-melting-point metal which constitutes the joining material and hence, it is possible to set the thickness of the low-melting-point metal layer 30- 20 to, for example, 1 μm whereby a thickness of the joining portion can be made extremely small thus reducing the connection resistance at the time of joining to an extremely small value. Accordingly, the present invention is particularly effective as a joining method in the power semiconductor which is required to suppress the generation of heat thereof. --

On Page 42, replace the second full paragraph with the following:

-- Next, in a state that the low-melting-point metal layer 20 and the first circuit ~~substrate~~ electrode 31 are arranged to face each other as shown in Fig. 1(b), the semiconductor die 10 is moved to the circuit board 30 side and is arranged such that the low-melting-point metal layer 20 and the first circuit electrode 31 are brought into contact with each other. Then, when the heating-and-pressurizing is performed in such a state at a temperature of 200°C or less, the low-melting-point metal layer 20 is melted and hence, the low-melting-point metal is diffused into the back-surface die electrode 11 and the first circuit electrode 31 by solid-liquid diffusion thus performing the first joining step.--